

*D'wet*

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer through a contact hole provided in said second insulating film, wherein said conductive layer and said second metallic layer are directly connected to each other at the bottom of a contact hole provided in said first insulating film.

*Sub F2*

7. (Twice Amended) A semiconductor device comprising:

*D<sup>2</sup>*

- a first insulating film comprising an organic material formed over a thin film transistor;
- a first metallic layer formed on said first insulating film;
- a second metallic layer formed on said first metallic layer;
- a second insulating film formed on said second metallic layer; and
- a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer through a contact hole provided in said second insulating film, wherein a source region or a drain region of said thin film transistor and said second metallic layer are directly connected to each other at the bottom of a contact hole provided in said first insulating film.

*Sub F3*

19. (Twice Amended) A semiconductor device comprising:

*D<sup>3</sup>*

- a first insulating film comprising an organic material formed over a thin film transistor;
- a first conductive layer formed on said first insulating film;
- a second conductive layer formed on said first conductive layer;
- a second insulating film formed on said second conductive layer; and
- a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein a source region or a drain region and said second conductive layer are directly connected to each other at the bottom of a contact hole provided in said first insulating film,

wherein said second conductive layer is contact with said first insulating film inside of said contact holes.

*D'Yer*  
*Subj*  
*D*

28. (Twice Amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer through a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer though a contact hole provided in said first insulating film.

*Subj*  
*D*

34. (Twice Amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

*Claim 1*

a second conductive layer formed on said first conductive layer;  
a second insulating film formed on said second conductive layer; and  
a pixel electrode formed on said second insulating film, said pixel electrode being connected  
to said second conductive layer through a contact hole provided in said second insulating film,  
wherein said second conductive layer is directly connected to said semiconductor layer  
through a contact hole provided in said first conductive layer and said first insulating film.

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*Claim 40*

40. (Amended) A semiconductor device comprising:  
a thin film transistor formed over a substrate, said thin film transistor having a semiconductor  
layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed  
therebetween;  
a first insulating film formed over said thin film transistor;  
a first wiring formed on said first insulating film;  
a second wiring formed on said first wiring;  
a second insulating film formed on said second wiring; and  
a pixel electrode formed on said second insulating film, said pixel electrode being connected  
to said second wiring through a contact hole provided in said second insulating film,  
wherein said second wiring is directly connected to said semiconductor layer though a  
contact hole provided in said first insulating film.

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#### REMARKS

The following remarks are in response to the Examiner's comments in the Advisory Action  
and rejections in the Final Rejection